

# **Selective enhancement of topologically induced interface states in a dielectric resonator chain**

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Nat. Commun. 6, 6710 (2015)

# Group information



## Prof. Henning Schomerus

- Department of Physics, Lancaster University
- 2 Ph.D students in his group

## Research interests

- Quantum transport including graphene
  - e.g. topological insulators
- Quantum optics, microlasers and photonics
  - PT-symmetric system, topologically protected states
- Quantum dynamical systems including atomic systems
  - Characterizing resonances in complex open systems

# PT symmetric system



PT symmetric Hamiltonian:  $(\text{PT})H(\text{PT}) = H$

$$H\phi_n = E_n\phi_n$$

$$H(\text{PT})\phi_n = (\text{PT})E_n\phi_n = \begin{cases} E_n(\text{PT})\phi_n & : \text{PT-exact phase (real eigenvalue)} \\ E_n^*(\text{PT})\phi_n & : \text{PT-broken phase (complex eigenvalue)} \end{cases}$$

(Example)

$$H = \begin{pmatrix} iV & g \\ g & -iV \end{pmatrix} \implies E_{\pm} = \pm\sqrt{g^2 - V^2} \quad \text{EP condition: } g = V$$

- At an EP, transition between two phases occurs.

# Topologically protected states

- Tight-binding Hamiltonian with disorder

$$\hat{H} = \begin{pmatrix} \ddots & \tilde{c}_1^2 & 0 & 0 & 0 & 0 & 0 \\ \tilde{c}_1^2 & -i\gamma & \tilde{c}_2^1 & 0 & 0 & 0 & 0 \\ 0 & \tilde{c}_2^1 & i\gamma & \tilde{c}_1^1 & 0 & 0 & 0 \\ 0 & 0 & \tilde{c}_1^1 & 0 & \tilde{c}_1^1 & 0 & 0 \\ 0 & 0 & 0 & \tilde{c}_1^1 & -i\gamma & \tilde{c}_2^1 & 0 \\ 0 & 0 & 0 & 0 & \tilde{c}_2^1 & i\gamma & \tilde{c}_1^2 \\ 0 & 0 & 0 & 0 & 0 & \tilde{c}_1^2 & \ddots \end{pmatrix}$$

$\tilde{c}_1, \tilde{c}_2$ : modulated coupling by disorder  
 $\gamma$ : decay rate

- Define the operators:

$$\hat{\sigma}_z = \begin{pmatrix} 1 & 0 & 0 \\ 0 & -1 & 0 \\ 0 & 0 & \ddots \end{pmatrix}, \quad \hat{\sigma}_x = \begin{pmatrix} 0 & 0 & 1 \\ 0 & 1 & 0 \\ \ddots & 0 & 0 \end{pmatrix} \rightarrow \hat{\sigma}_x \hat{H}^\dagger \hat{\sigma}_x = \hat{H} \quad ([\hat{H}, \mathcal{PT}] = 0, \text{ PT-symmetric})$$

- Then,

$$\det(\hat{H}) = \det(\hat{\sigma}_x \hat{H}^\dagger \hat{\sigma}_x) = \det(\hat{H}^\dagger)$$

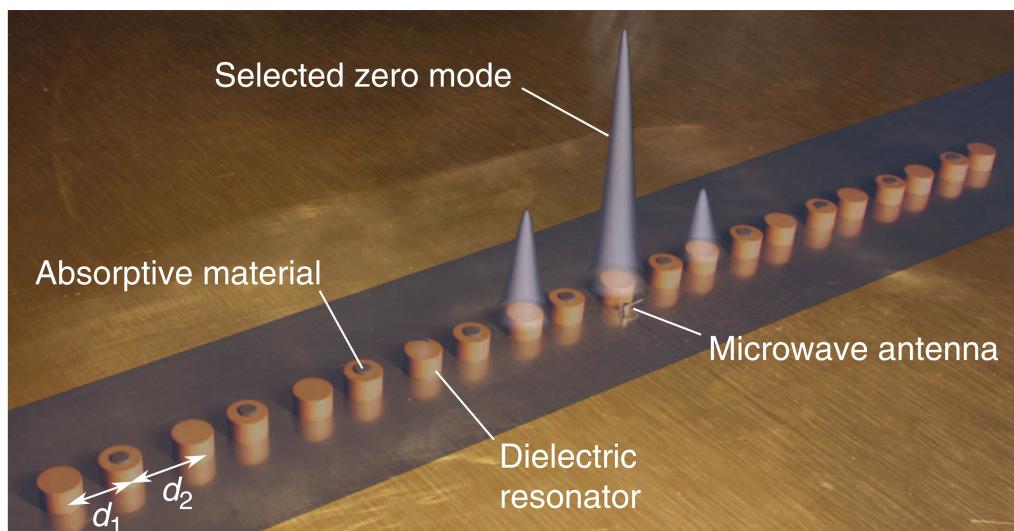
$$\det(\hat{H}) = (-1)^{2 \cdot (N-1)/2} \det(-\hat{H}^\dagger) = \det(-\hat{H}^\dagger) = (-1)^N \det(\hat{H}^\dagger) \quad (\hat{\sigma}_x \hat{\sigma}_z \hat{H} \hat{\sigma}_z \hat{\sigma}_x = -\hat{H})$$

$\rightarrow \boxed{\det(\hat{H}) = (-1)^N \det(\hat{H})} \rightarrow \det(\hat{H}) = 0$

(N=odd in this system,  
zero-eigenvalue always exists)

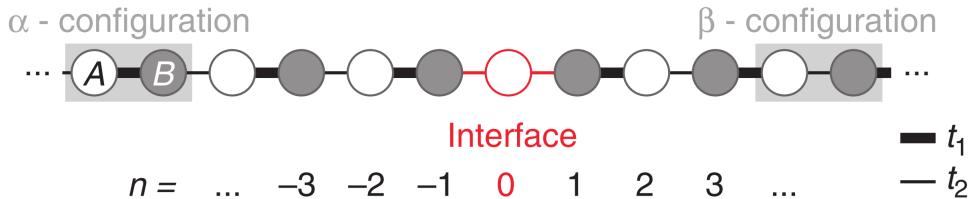
# Realization of dimer chains

a



- (a): Picture of experimental microwave resonator chain
- (b): Schematic of the chain. A (white) and B (grey) indicate the sublattice.  $t_1$  and  $t_2$  denote the coupling strength.
- Coupling controlled by varying the spacing between resonators.

b

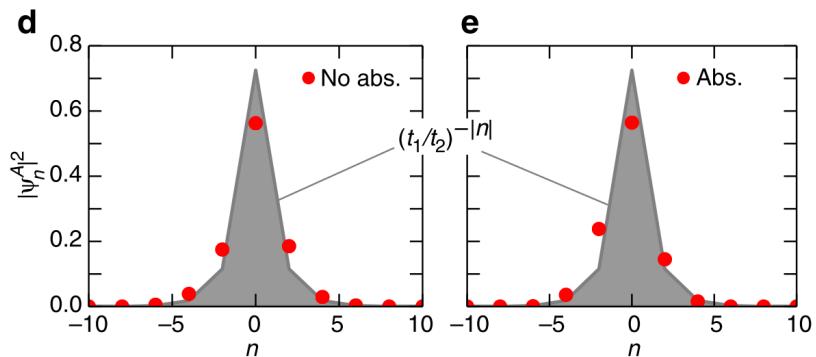
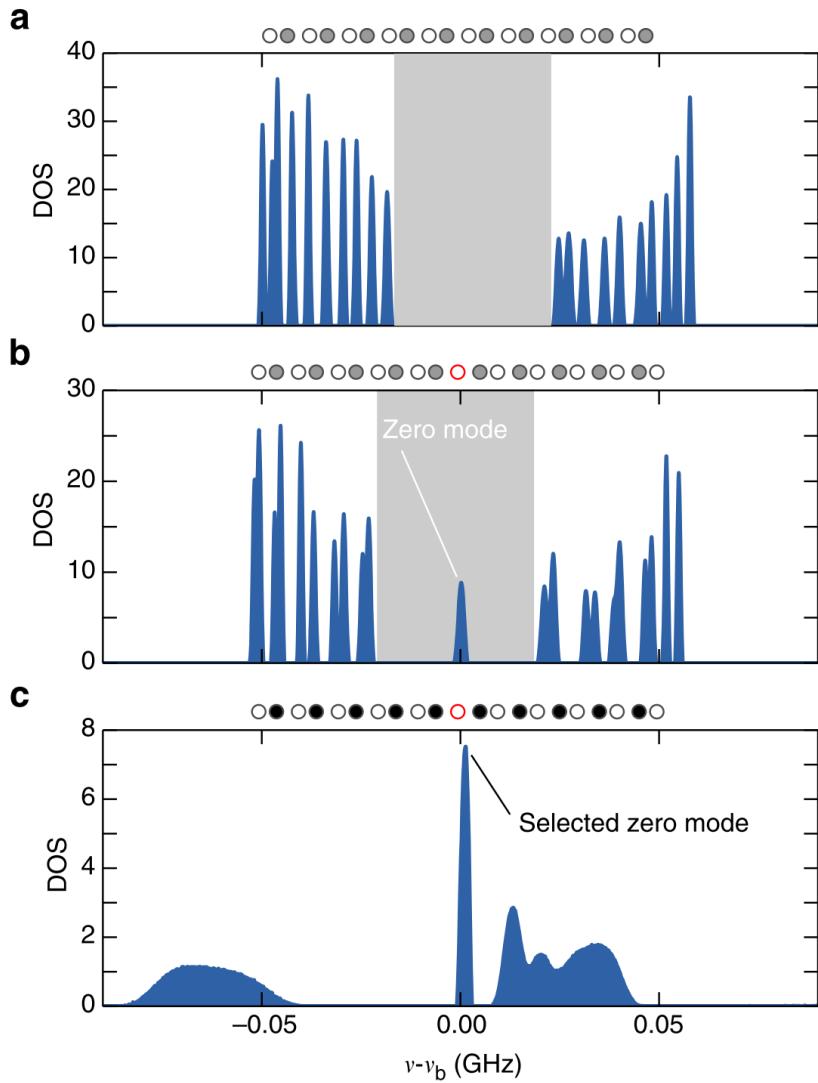


$$(\alpha) \begin{cases} (v - v_n)\psi_n = t_2\psi_{n-1} + t_1\psi_{n+1}, & n = -2, -4, \dots \\ (v - v_n)\psi_n = t_1\psi_{n-1} + t_2\psi_{n+1}, & n = -1, -3, \dots, \end{cases}$$

Described by tight-binding equations: interface  $\{(v - v_0)\psi_0 = t_2(\psi_{-1} + \psi_1),$

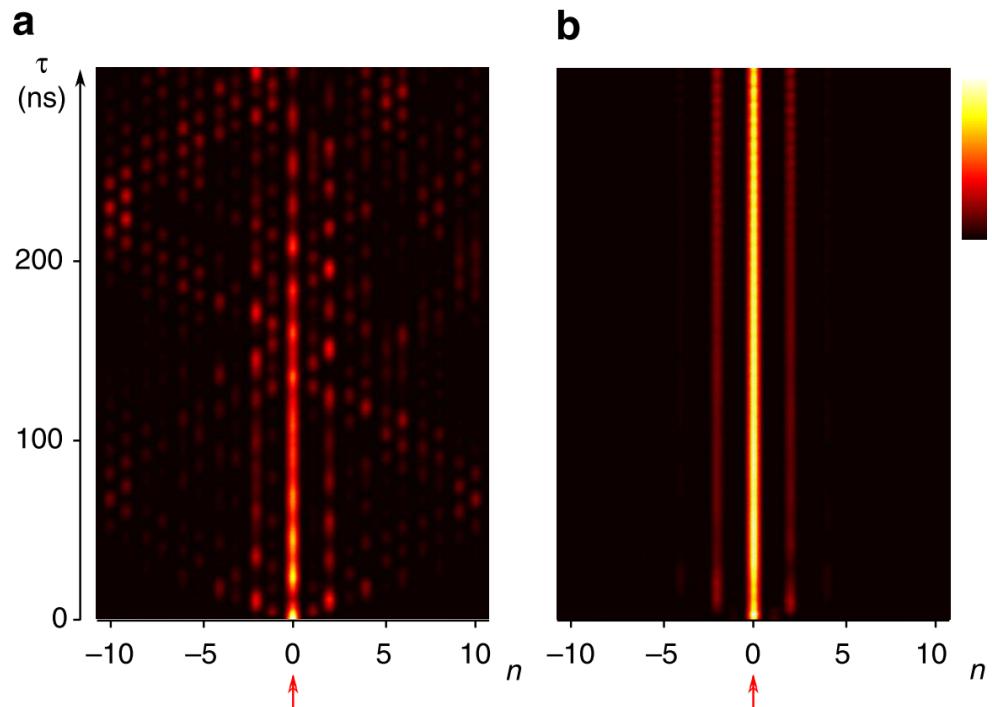
$$(\beta) \begin{cases} (v - v_n)\psi_n = t_2\psi_{n-1} + t_1\psi_{n+1}, & n = 1, 3, \dots, \\ (v - v_n)\psi_n = t_1\psi_{n-1} + t_2\psi_{n+1}, & n = 2, 4, \dots, \end{cases}$$

# Density of states and zero-mode profiles



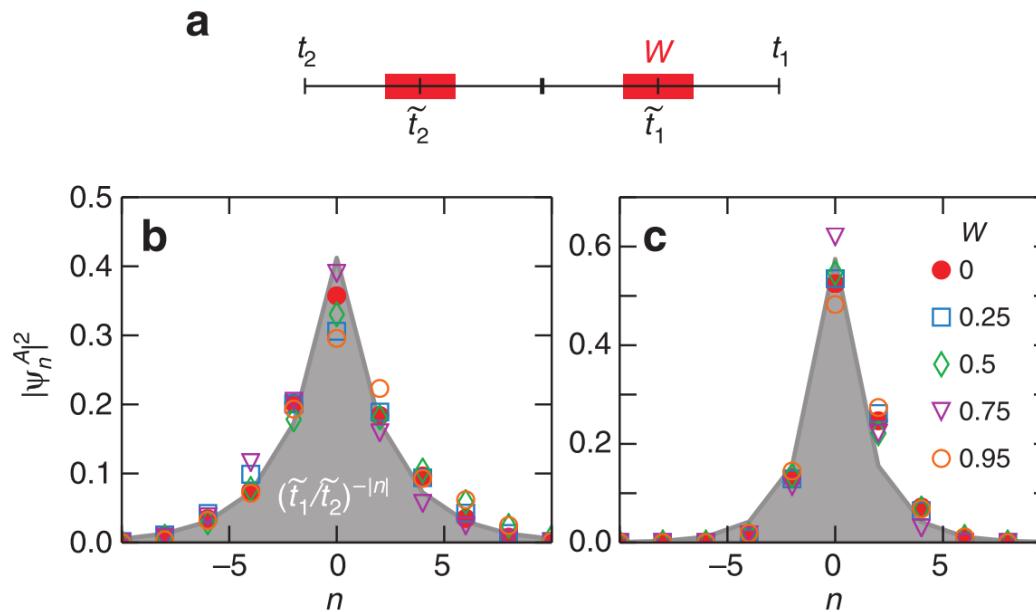
- (a) DOS for a defectless chain
  - (b) DOS with a defect
  - (c) DOS with a defect and absorption on B sites
  - (d) Intensity profile of zero-mode on A sites
  - (e) Intensity profile of zero-mode on A sites with absorption on B sites
- ➔ **Visibility of the zero mode enhanced in frequency domain**

# Selective enhancement of the zero mode



- (a) Time evolution of the field intensity when pulse launched on the defect site without absorption on B sites.
  - (b) With absorption on B sites. It shows that adding losses drastically enhances the visibility of the zero-mode.
- Visibility enhanced in time domain

# Robustness of the zero mode against structural disorder



- (a) Randomized coupling strengths  $(\tilde{t}_1, \tilde{t}_2)$  and disorder strength ( $W$ )
  - (b) Zero-mode intensity profiles on A sites without losses
  - (c) Zero-mode intensity profiles with losses on the B sites.
- ➔ Zero mode is invariant under random variation of coupling strength, which shows the robustness against structural disorder

# Summary

- Topologically induced defect state in a chain of dielectric microwave cavity resonators realized.
- It was shown that visibility of the defect state could be enhanced both in frequency and time domain by imposing losses.
- This mode selection mechanism carries over wide range of topological and PT-symmetric optical platforms.